	Application No.	Applicant(s)
Notice of Allowability	10/017,855	FISHER ET AL.
	Examiner	Art Unit
	Julio J. Maldonado	2823
The MAILING DATE of this communication appears on the cover sheet with the correspondence address All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS. This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308. 1. This communication is responsive to response mailed on 05/03/2004. 2. The allowed claim(s) is/are 1-14 and 21-26.		
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3. ☑ The drawings filed on <u>06 February 2004</u> are accepted by the Examiner.		
 4. Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some* c) None of the: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No. 3. Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements 		
noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.	ENT of this application.	
5. A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.		
6. CORRECTED DRAWINGS (as "replacement sheets") mus (a) including changes required by the Notice of Draftspers 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Examiner's Paper No./Mail Date ldentifying indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in the	on's Patent Drawing Review (PTO- c Amendment / Comment or in the C	Office action of action of the back) of
7. DEPOSIT OF and/or INFORMATION about the depos attached Examiner's comment regarding REQUIREMENT R		
 Attachment(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/06 Paper No./Mail Date	6. ⊠ Interview Summary Paper No./Mail Dat 8), 7. ⊠ Examiner's Amendr	ie <u>20040702</u> .

DETAILED ACTION

EXAMINER'S AMENDMENT

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Joseph N. Ziebert (Reg. No. 35,421) on 07/01/2004.

The application has been amended as follows:

Claim 8, lines 3-4, recites "... E-beam irradiating a gate pattern of a photoresist layer; trimming the E-beam irradiated gate pattern...", change to --curing a gate pattern of a photoresist layer using E-beam irradiation; trimming the cured E-beam irradiated gate pattern--.

Claim 8, line 8, recites "...70 nm...", change to --70 nm, wherein a variation of the width along the length of the transistor gate is reduced due to the curing step--; Claim 9, line 1 recites "... wherein the E-beam irradiation step uses...", change to --wherein said E-beam irradiation uses--.

Claim 14, line 1 recites "... wherein the E-beam radiation step achieves...", change to --wherein said E-beam irradiation achieves--; Claim 21, lines 2-4 recites "... irradiating a portion of the photoresist material with an electron beam to form a gate pattern; trimming the gate pattern...", change to --curing a portion of the photoresist

material by irradiating said portion of the photoresist material with an electron beam to form a gate pattern; trimming the cured gate pattern--.

Claim 21, line 6 recites, "...70 nm...", change to --70 nm, wherein a variation of width along the length of the transistor gate is reduced due to the curing step--.

Allowable Subject Matter

- 2. Claims 1-14 and 21-26 allowed.
- 3. The following is an examiner's statement of reasons for allowance: the prior art of record, Tsai et al. to U.S. 6,183,937 B1 and Auda et al. to U.S. 5,139,904 fail to teach curing a gate pattern followed by trimming said cured gate pattern, wherein a variation of the width along the length of the transistor gate is reduced due to the curing step.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

- 4. Any inquiry concerning this communication or earlier communications from the examiner should be directed to examiner Julio J. Maldonado whose telephone number is (571) 272-1864. The examiner can normally be reached on Monday through Friday.
- 5. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri, can be reached on (571) 272-1855. The fax number for this group is 703-872-9306 for before final submissions, 703-872-9306 for after final

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submissions and the customer service number for group 2800 is (703) 306-3329.

Updates can be found at http://www.uspto.gov/web/info/2800.htm.

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Julio J. Maldonado July 2, 2004

George Fourson
Primary Examiner